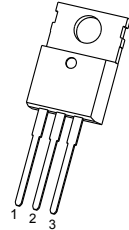


**TO-220-3L-C Plastic-Encapsulate MOSFETS****CJP80N04 N-Channel Power MOSFET**

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
40V	7mΩ@10V	80A
	20mΩ@4.5V	

TO-220-3L-C

1. GATE
2. DRAIN
3. SOURCE

**DESCRIPTION**

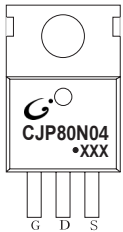
The CJP80N04 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

FEATURES

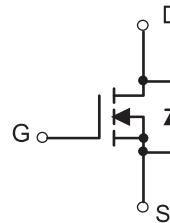
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

APPLICATIONS

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible Power Supply

MARKING

CJP80N04= Device code
Solid dot = Green molding compound device,
if none, the normal device
XXX=Date Code

EQUIV ALENT CIRCUIT**MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	80	A
Pulsed Drain Current	I_{DM}	320	A
Single Pulsed Avalanche Energy	$E_{AS}^{(1)}$	350	mJ
Power Dissipation	P_D	2	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	$^{\circ}\text{C}$

(1). E_{AS} condition: $V_{DD}=20\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$, Starting $T_J = 25^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

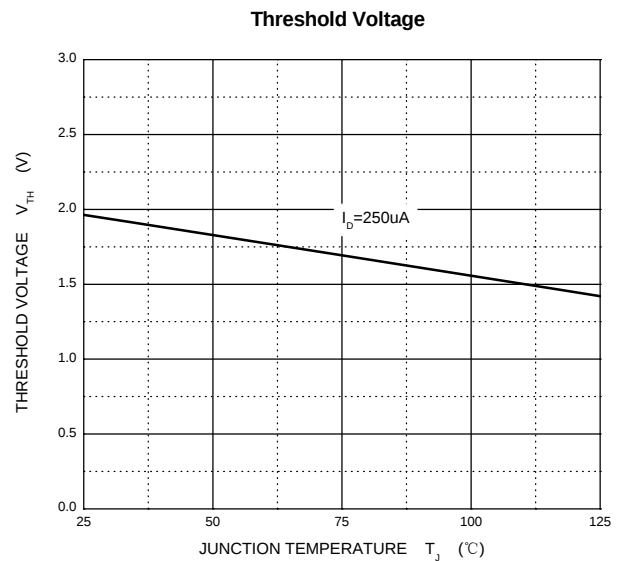
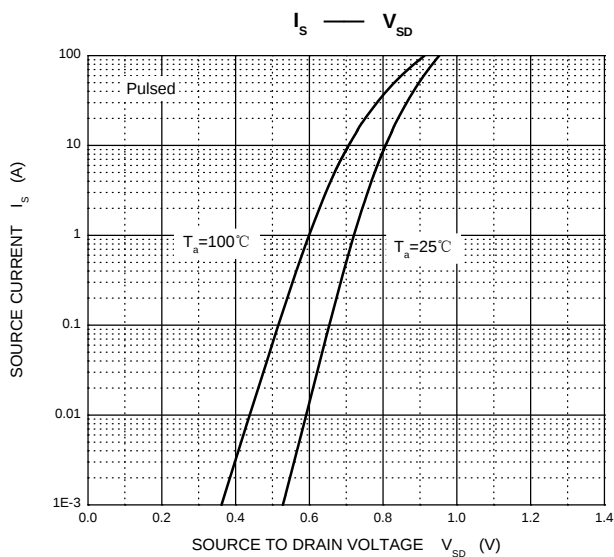
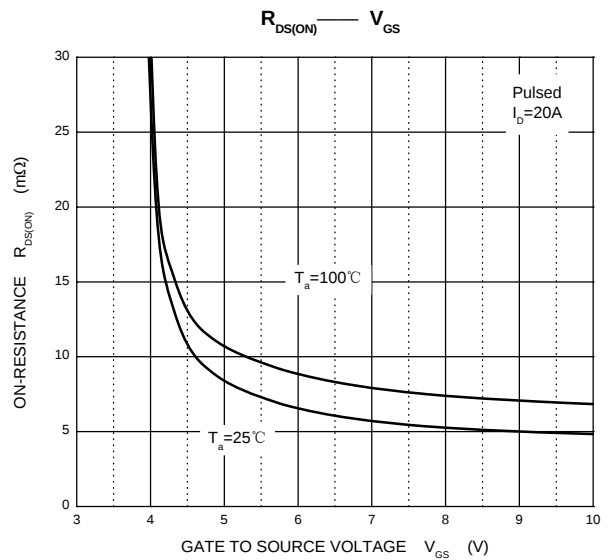
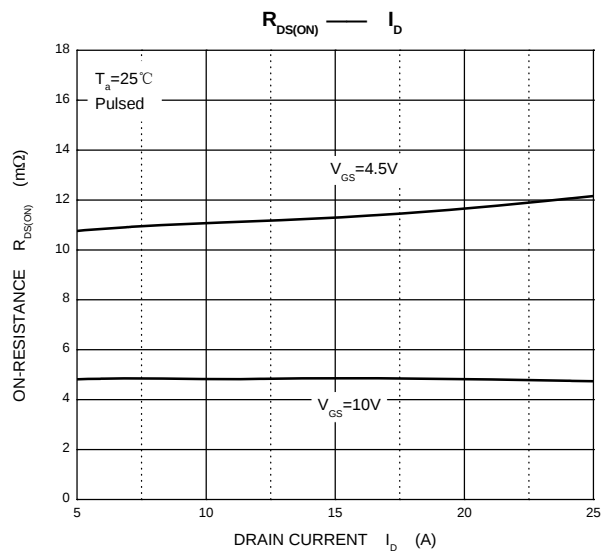
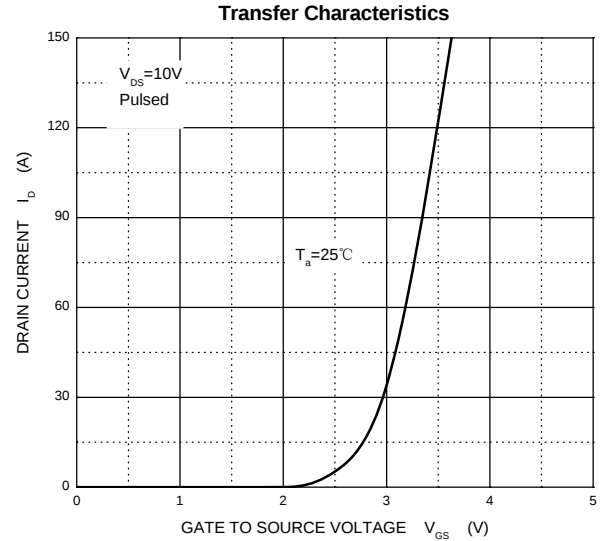
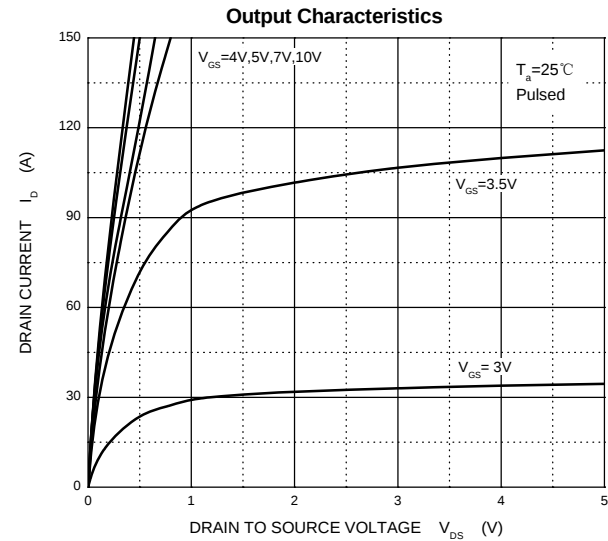
$T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off characteristics						
Drain-source breakdown voltage	$V_{(BR) DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
On characteristics (note1)						
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.2	2	2.5	V
Static drain-source on-sate resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		5.5	7	m Ω
		$V_{GS} = 4.5V, I_D = 20A$		12	20	m Ω
Forward transconductance	g_{FS}	$V_{DS} = 10V, I_D = 20A$		20		S
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = 20V, V_{GS} = 0V,$ $f = 1MHz$		4010		pF
Output capacitance	C_{oss}			750		
Reverse transfer capacitance	C_{rss}			390		
Switching characteristics (note 2)						
Total gate charge	Q_g	$V_{DS} = 20V, V_{GS} = 10V,$ $I_D = 20A$		50		nC
Gate-source charge	Q_{gs}			12		
Gate-drain charge	Q_{gd}			13		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 20V,$ $V_{GS} = 10V, R_G = 3\Omega,$ $R_L = 1\Omega$		11		ns
Turn-on rise time	t_r			10		
Turn-off delay time	$t_{d(off)}$			38		
Turn-off fall time	t_f			11		
Drain-Source Diode Characteristics						
Drain-source diode forward voltage(note1)	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V
Continuous drain-source diode forward current	I_S				80	A
Pulsed drain-source diode forward current	I_{SM}				320	A

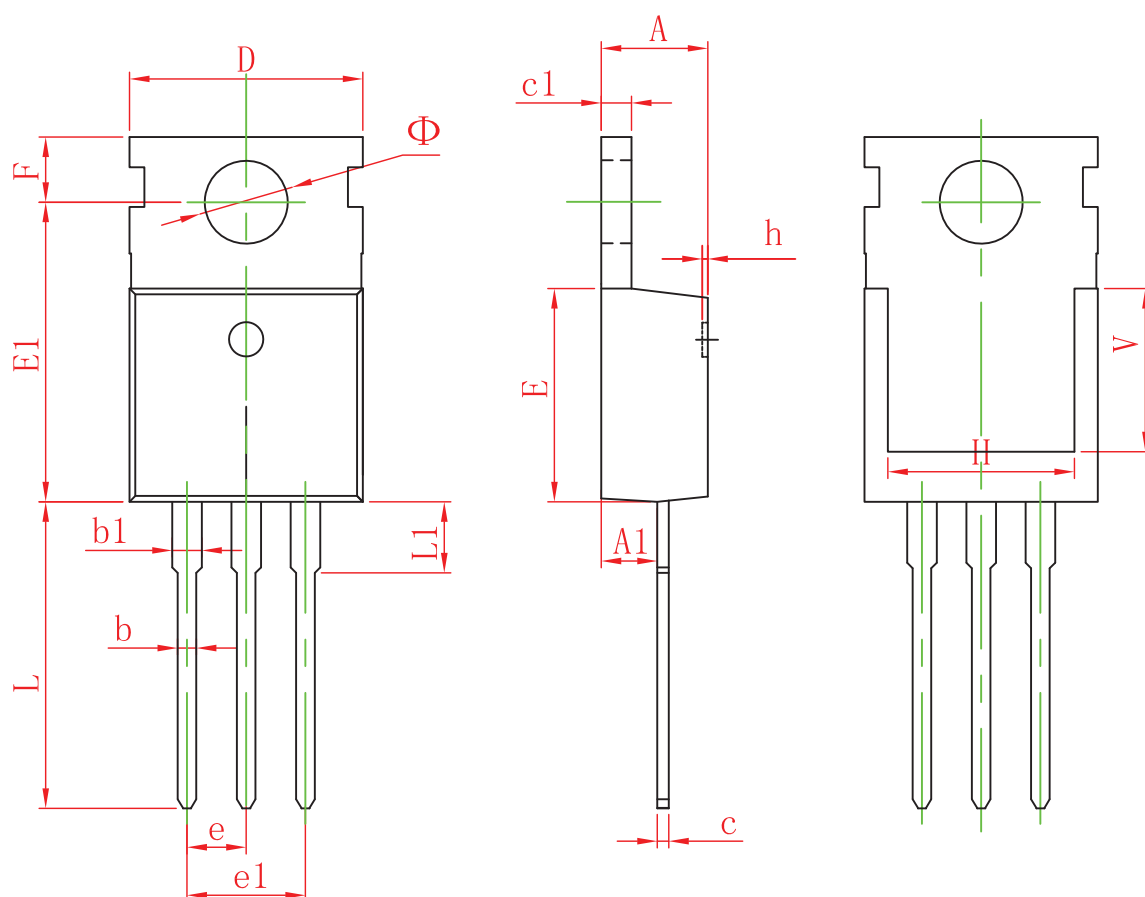
Notes:

1. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
2. Guaranteed by design, not subject to production.

Typical Characteristics



TO-220-3L-C Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150